

Supplementary Information for

Reliable resistive switching memory based on oxygen-vacancy-controlled bilayer structures

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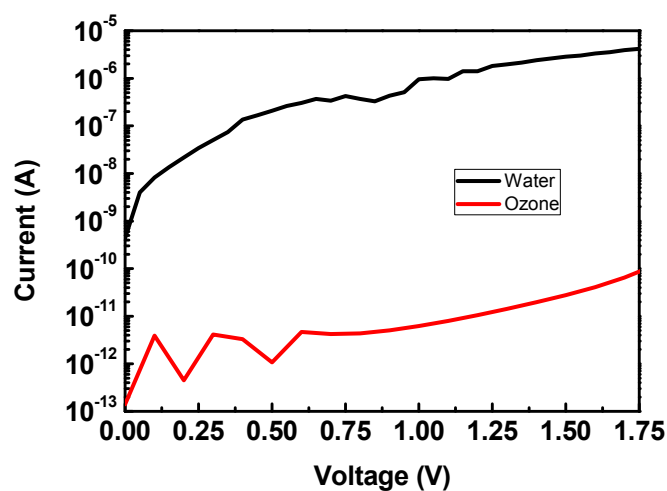


Fig. S1. Comparison of initial states of RRAM devices with a single layer of AlO_x using different oxidizers.

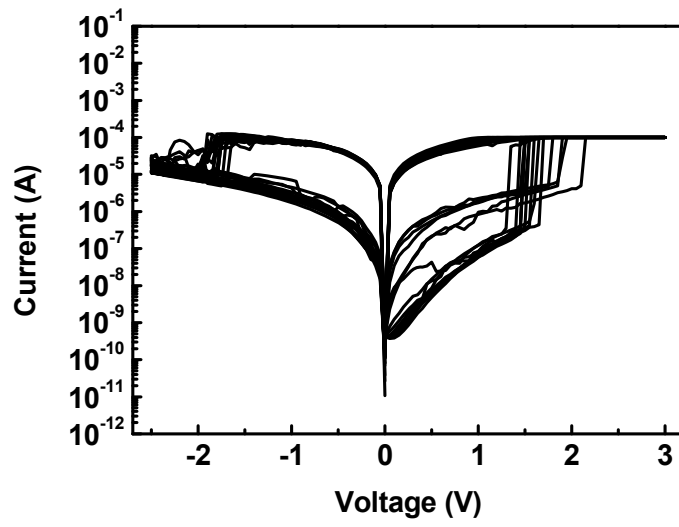


Fig. S2. Resistive switching behavior of single-layer RRAM device with AlO_x (water).